

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 8 A, 650 V, D2, DPAK

FFSD0865B

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

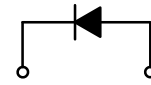
- Max Junction Temperature 175 C
- Avalanche Rated 33 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- These Devices are Pb Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
-	μ		
	μ		
-			
		-	

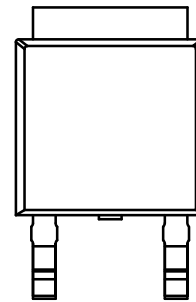


Schottky Diode



DPAK
CASE 369AS

MARKING DIAGRAM



ORDERING INFORMATION

FFSD0865B

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
--	θ		

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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ON CHARACTERISTICS

			-			
			-			
			-			
			-			μ
			-			
			-			

CHARGES, CAPACITANCES & GATE RESISTANCE

			-		-	
			-		-	
			-		-	
			-		-	

PART MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity

FFSD0865B

TYPICAL CHARACTERISTICS

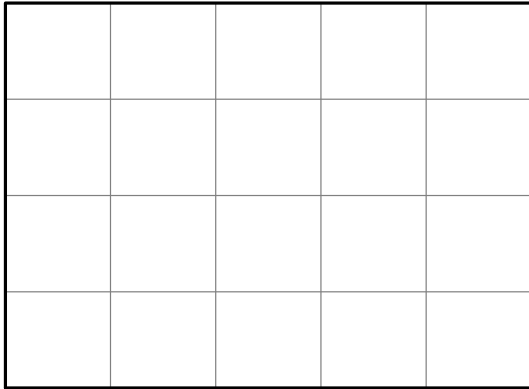


Figure 1. Forward Characteristics

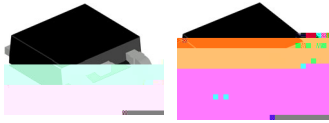
Figure 2. Reverse Characteristics

Figure 3. Current Derating

Figure 4. Power Derating

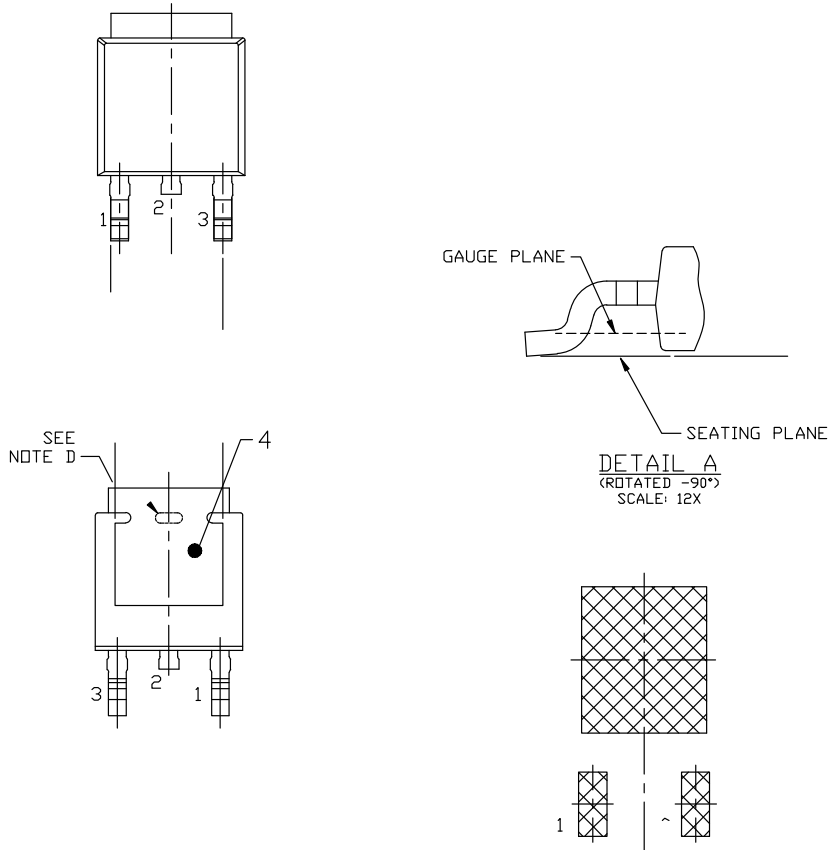
Figure 5. Capacitive Charge vs. Reverse Voltage

Figure 6. Capacitance vs. Reverse Voltage



DPAK3 6.10x6.54x2.29, 4.57P
CASE 369AS
ISSUE B

DATE 20 DEC 2023



LAND PATTERN RECOMMENDATION

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Assembly Lot Code

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